

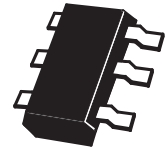
## SuperSOT™ 15V NPN SILICON LOW SATURATION SWITCHING TRANSISTOR

### SUMMARY

$V_{CE0}=15V$ ;  $R_{SAT} = 50m\Omega$ ;  $I_C = 4A$

### DESCRIPTION

This new 4th generation ultra low saturation transistor utilises the Zetex matrix structure combined with advanced assembly techniques to give extremely low on state losses. This makes it ideal for high efficiency, low voltage switching applications.



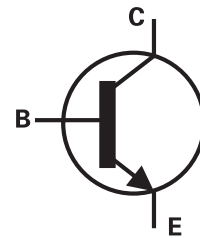
SOT23-6

### FEATURES

- Low Equivalent On Resistance
- Extremely Low Saturation Voltage
- $h_{FE}$  characterised up to 12A
- $I_C=4A$  Continuous Collector Current
- SOT23-6 package

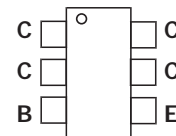
### APPLICATIONS

- DC - DC Converters
- Power Management Functions
- Power switches
- Motor control



### ORDERING INFORMATION

DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
ZXT10N15DE6TA	7	8mm embossed	3000 units
ZXT10N15DE6TC	13	8mm embossed	10000 units



Top View

### DEVICE MARKING

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# ZXT10N15DE6

## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-Base Voltage	$V_{CBO}$	15	V
Collector-Emitter Voltage	$V_{CEO}$	15	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Peak Pulse Current	$I_{CM}$	13	A
Continuous Collector Current	$I_C$	4	A
Base Current	$I_B$	500	mA
Power Dissipation at $T_A=25^\circ\text{C}$ (a) Linear Derating Factor	$P_D$	1.1 8.8	W mW/ $^\circ\text{C}$
Power Dissipation at $T_A=25^\circ\text{C}$ (b) Linear Derating Factor	$P_D$	1.7 13.6	W mW/ $^\circ\text{C}$
Operating and Storage Temperature Range	$T_J:T_{stg}$	-55 to +150	$^\circ\text{C}$

## THERMAL RESISTANCE

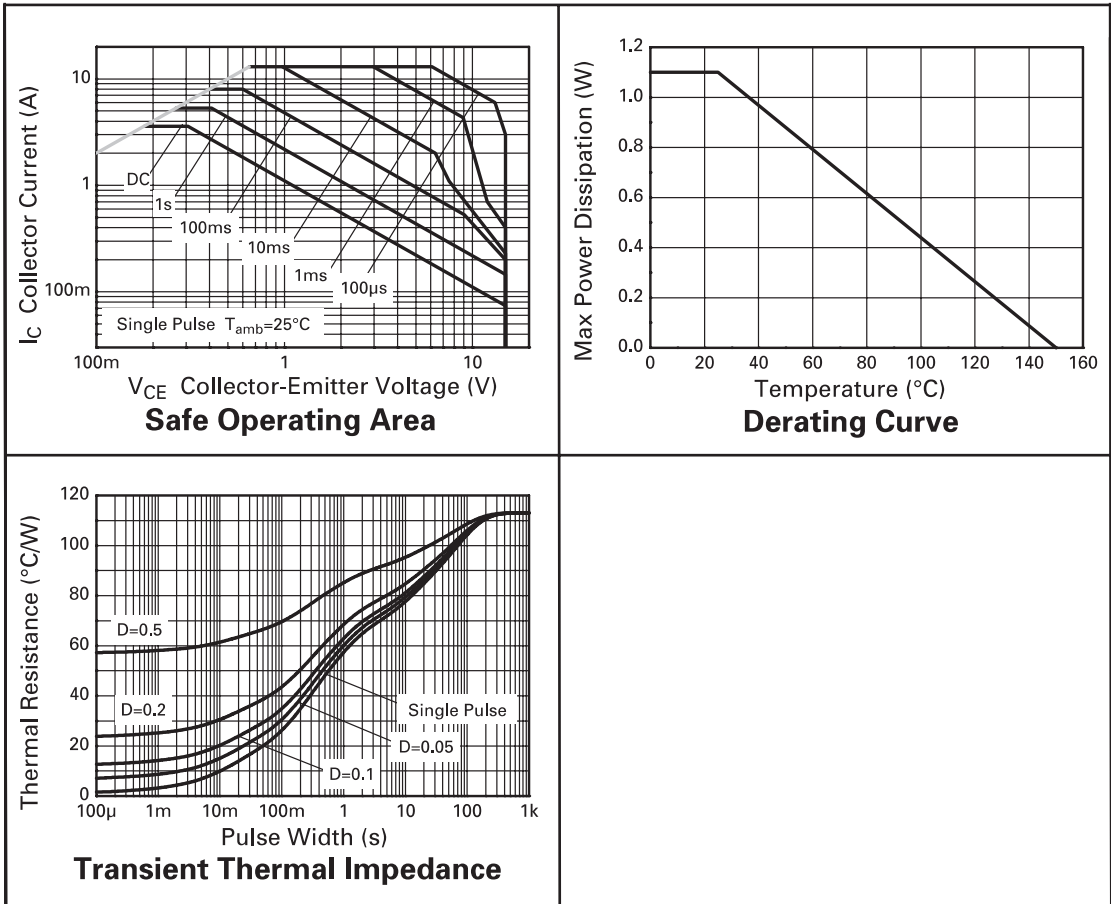
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	113	$^\circ\text{C/W}$
Junction to Ambient (b)	$R_{\theta JA}$	73	$^\circ\text{C/W}$

### NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at  $t \leq 5$  secs.

## TYPICAL CHARACTERISTICS



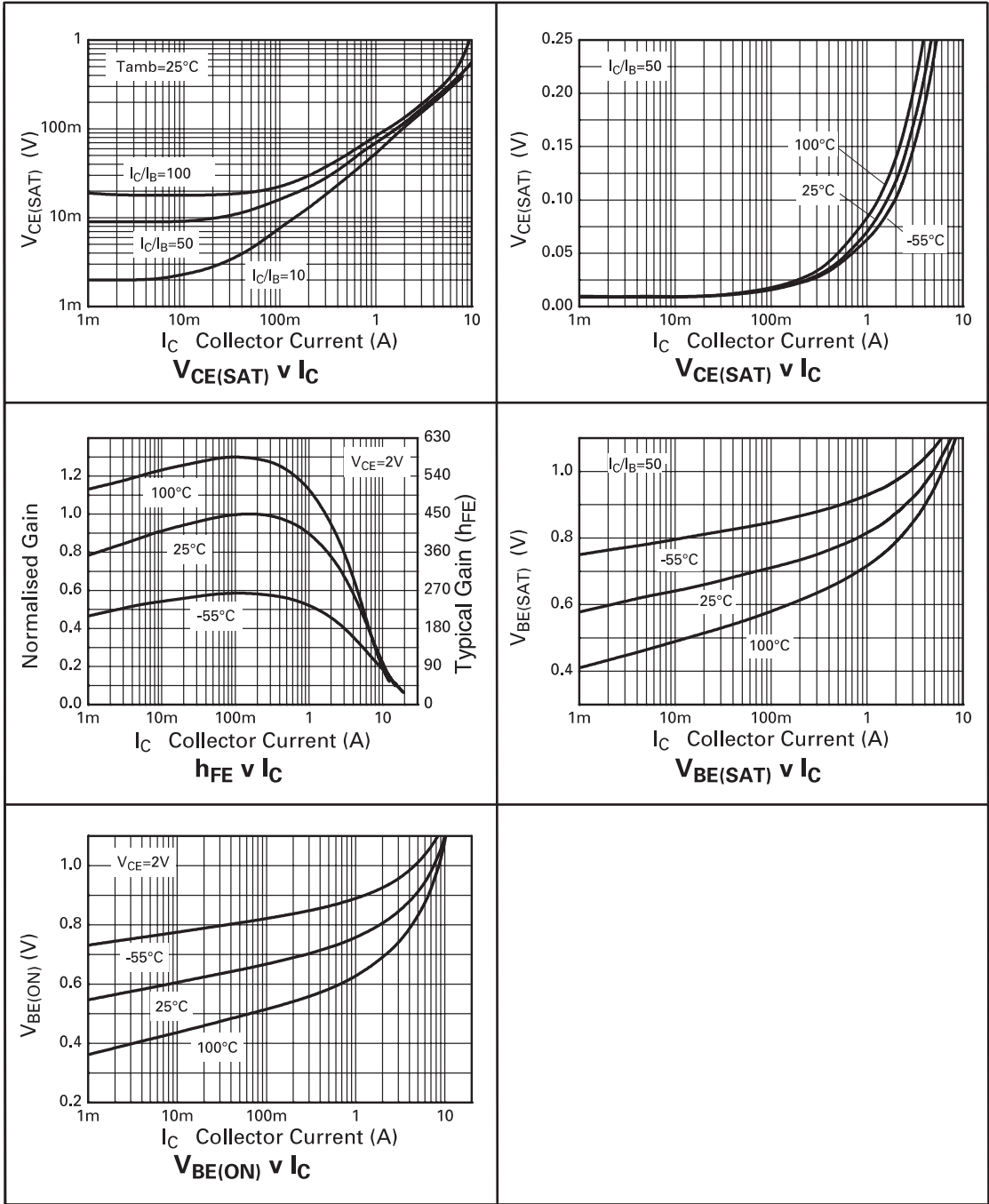
# ZXT10N15DE6

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	15	70		V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	15	18		V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	8.2		V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	$I_{CBO}$			100	nA	$V_{CB}=10\text{V}$
Emitter Cut-Off Current	$I_{EBO}$			100	nA	$V_{EB}=4\text{V}$
Collector Emitter Cut-Off Current	$I_{CES}$			100	nA	$V_{CES}=10\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		8 70 165 230	14 100 200 260	mV mV mV mV	$I_C=0.1\text{A}, I_B=10\text{mA}^*$ $I_C=1\text{A}, I_B=10\text{mA}^*$ $I_C=3\text{A}, I_B=50\text{mA}^*$ $I_C=4\text{A}, I_B=50\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		0.94	1.0	V	$I_C=4\text{A}, I_B=50\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		0.87	0.95	V	$I_C=4\text{A}, V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	200 300 200 150	415 450 320 240 80			$I_C=10\text{mA}, V_{CE}=2\text{V}^*$ $I_C=0.2\text{A}, V_{CE}=2\text{V}^*$ $I_C=3\text{A}, V_{CE}=2\text{V}^*$ $I_C=5\text{A}, V_{CE}=2\text{V}^*$ $I_C=12\text{A}, V_{CE}=2\text{V}^*$
Transition Frequency	$f_T$	80	120		MHz	$I_C=50\text{mA}, V_{CE}=10\text{V}$ $f=100\text{MHz}$
Output Capacitance	$C_{obo}$		30	40	pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Turn-On Time	$t_{(on)}$		120		ns	$V_{CC}=10\text{V}, I_C=3\text{A}$ $I_{B1}=I_{B2}=50\text{mA}$
Turn-Off Time	$t_{(off)}$		160		ns	

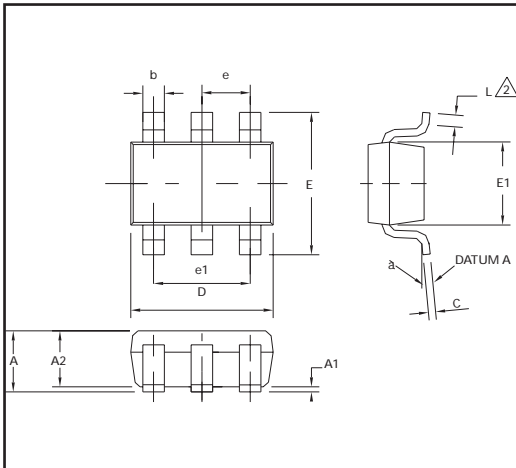
\*Measured under pulsed conditions. Pulse width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$

## TYPICAL CHARACTERISTICS

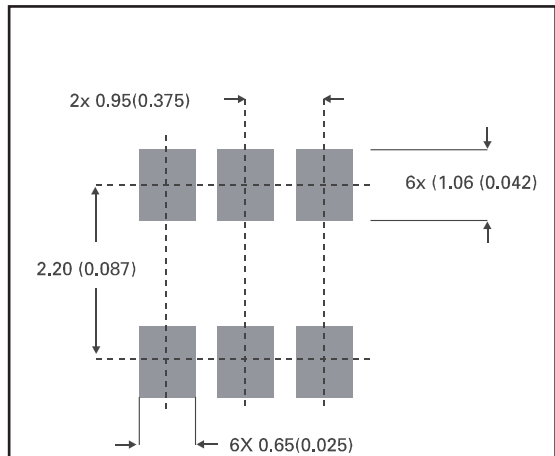


# ZXT10N15DE6

## PACKAGE DIMENSIONS



## PAD LAYOUT DETAILS



DIM	Millimetres		Inches	
	Min	Max	Min	Max
A	0.90	1.45	0.35	0.057
A1	0.00	0.15	0	0.006
A2	0.90	1.30	0.035	0.051
b	0.35	0.50	0.014	0.019
C	0.09	0.20	0.0035	0.008
D	2.80	3.00	0.110	0.118
E	2.60	3.00	0.102	0.118
E1	1.50	1.75	0.059	0.069
L	0.10	0.60	0.004	0.002
e	0.95 REF		0.037 REF	
e1	1.90 REF		0.074 REF	
L	0°	10°	0°	10°



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ISSUE 1 - SEPTEMBER 2000